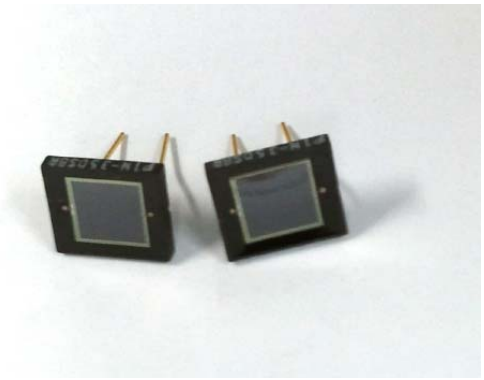
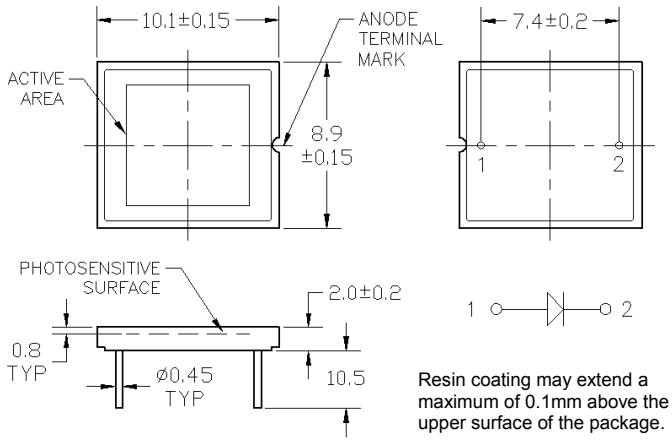
PIN-035DQR
Silicon Photodiode with Clear Resin



Package Dimensions in mm



Resin coating may extend a maximum of 0.1mm above the upper surface of the package.

FEATURES

- Clear Resin Coating
- Low Capacitance
- High Shunt Resistance

APPLICATIONS

- Spectrophotometer
- Analytical Instruments
- Medical Instruments

DESCRIPTION:

PIN-035DQR is a Silicon photodiode sensitive to 320-1100nm. It is packaged in a 2-pins ceramic with clear resin potting. The low capacitance and high shunt resistance makes it ideal for spectroscopy, fluorescence application, and analytical instrument.

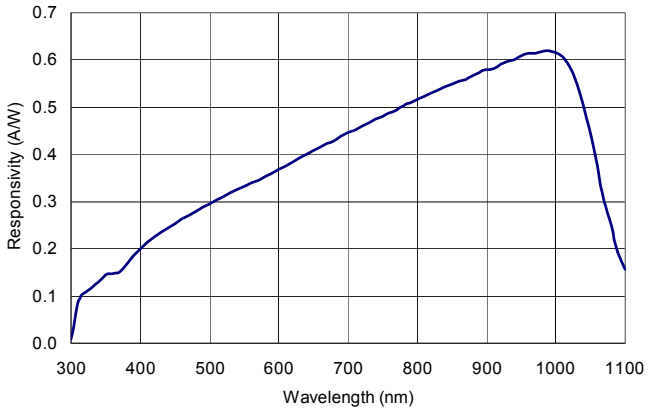
ELECTRO-OPTICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

PARAMETER	SYMBOL	CONDITION	MIN	TYP	MAX	UNITS
Active Area Size				5.8 x 5.8		mm
Effective Active Area	AA			34		mm^2
Spectral Range	S		320		1100	nm
Responsivity	Rλ	320nm		0.1		A/W
		633nm		0.4		
		980nm (peak)		0.6		
Shunt Resistance	Rsh	-10mV	0.1	0.4		G. Ohm
Capacitance	Ct	0V		380		pF
Rise Time	tr	0V, 1 K.Ohm		1		µs
Reverse Voltage	Vr				5	V
Operating Temperature	Topr		-20 to +60			°C
Storage Temperature	Tstg		-20 to +80			°C

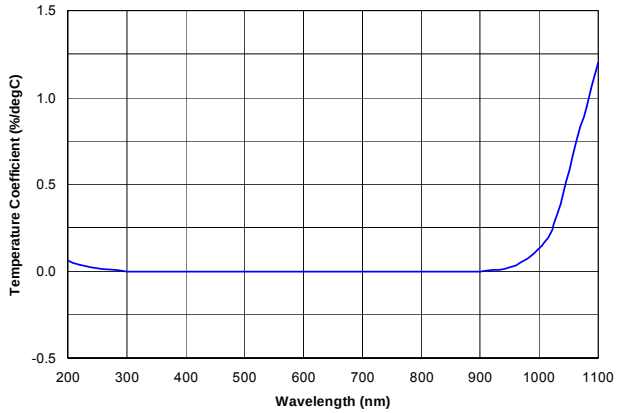
12525 Chadron Avenue, Hawthorne, CA 90250, USA
Tel +1 310-978-0516 Fax +1 310-644-1727 www.osioptoelectronics.com

PIN-035DQR
Silicon Photodiode with Clear Resin

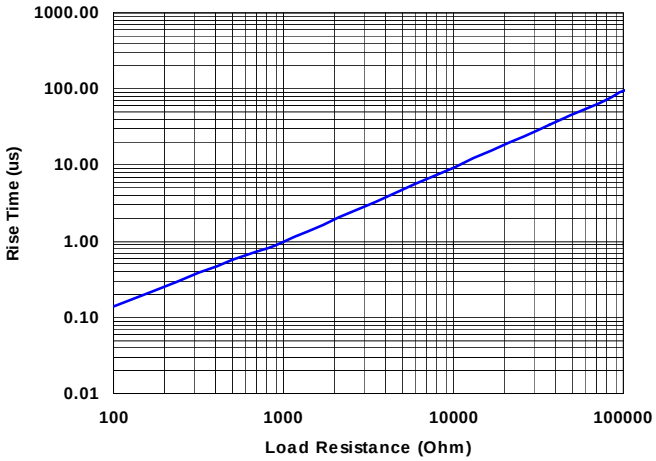
Typical Responsivity (T_A = 25°C)



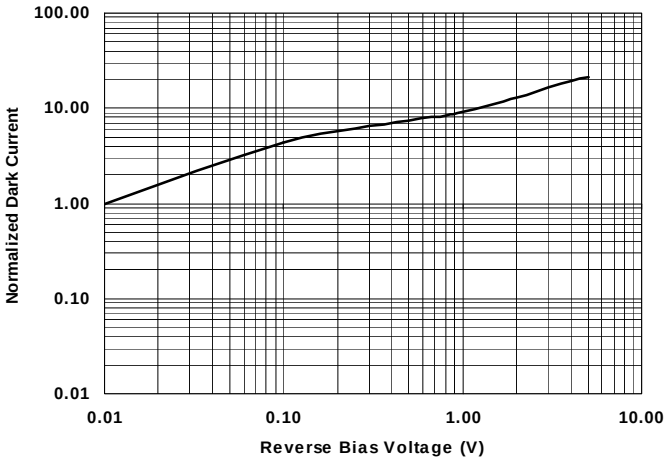
Typ. Photo-sensitivity temperature characteristic



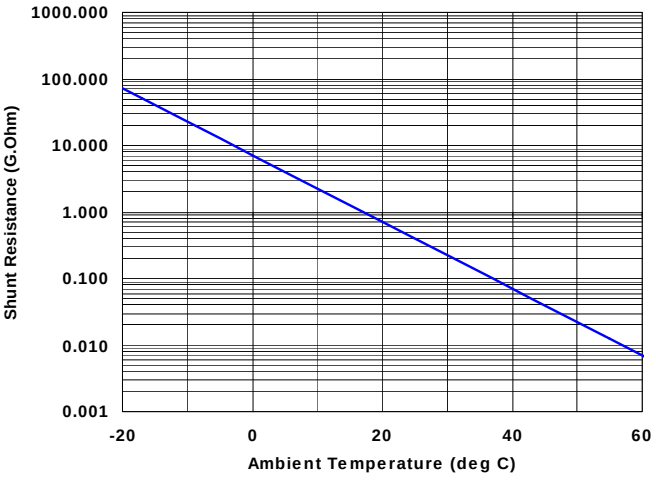
Typ. Rise Time vs Load Resistance (T_A = 25°C, Vr =0V)



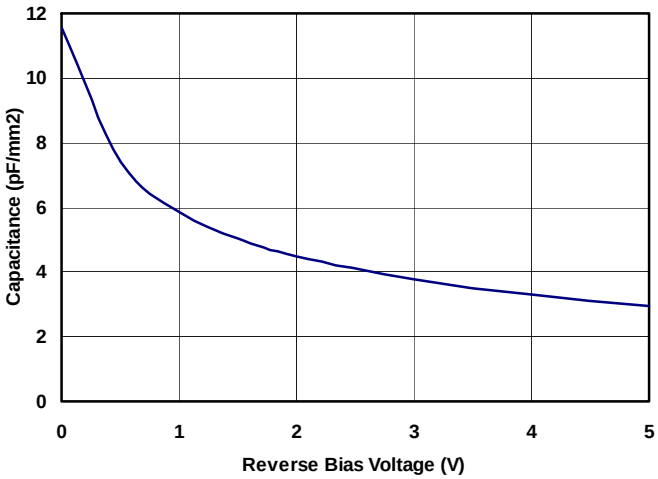
Typ. Dark Current (T_A = 25°C, Normalized at -0.01V)



Typ. Shunt Resistance vs Ambient Temperature (Vr=10mV)



Typical Capacitance vs Reverse Bias (T_A = 25°C)



12525 Chadron Avenue, Hawthorne, CA 90250, USA
Tel +1 310-978-0516 Fax +1 310-644-1727 www.osioptoelectronics.com